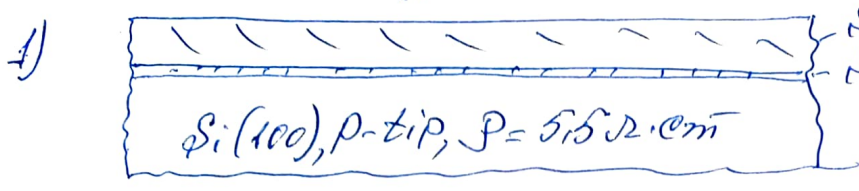
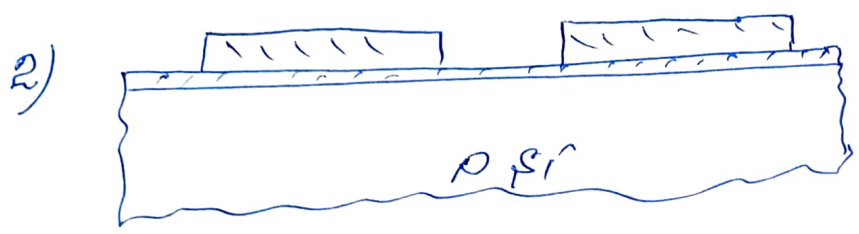


Tehnologie CMOS (pentru proiect de an)



- 1) placeta initiala
- 2) Oxidarea termica
- 2) Depunerea Si3N4



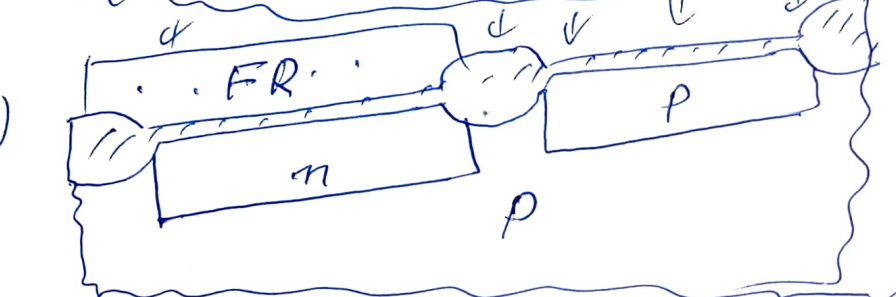
1 FL. Corodarea lui Si3N4



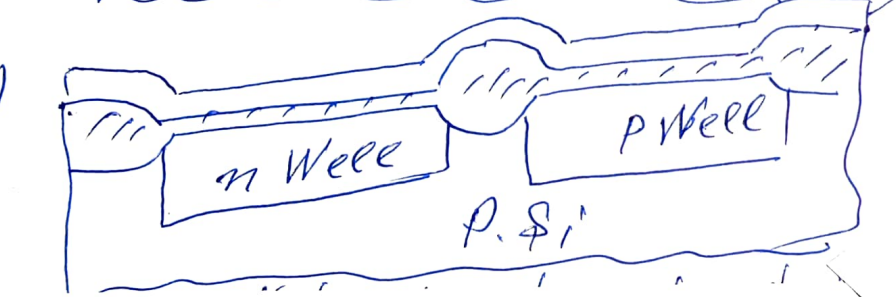
Tehnica LOCOS



- 1) Inlaturarea Si3N4 in H3PO4 (70°C)
- 2) 2 FL
- 3) Implantarea P3+

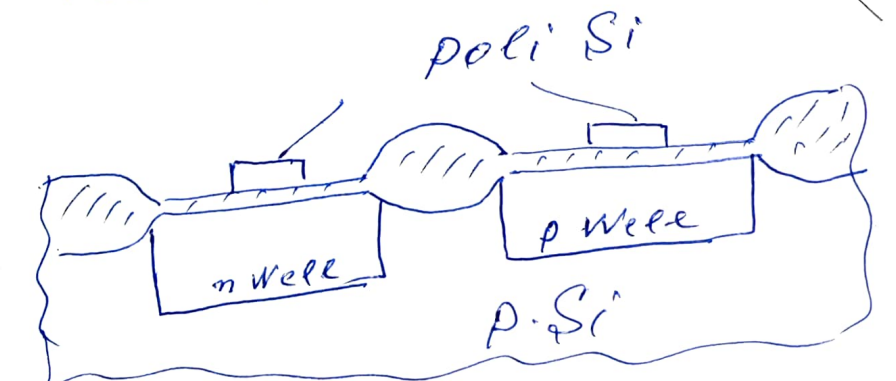


- 1) 3 FL
- 2) Implantarea Bii

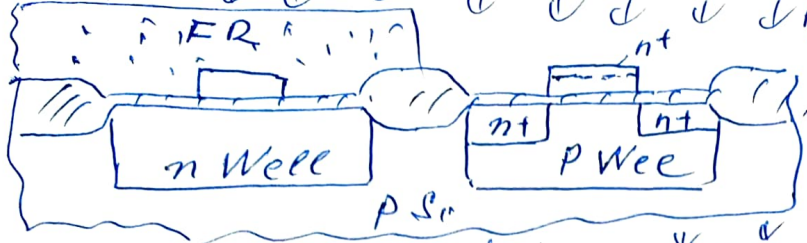


poli Si

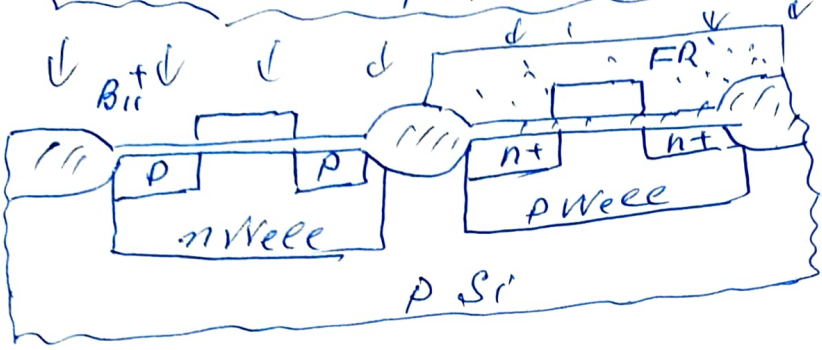
- 1) Inlaturarea FR
 - 2) Depunerea poli Si
- $SiH_4 \xrightarrow{600^\circ C} Si + 2H_2$



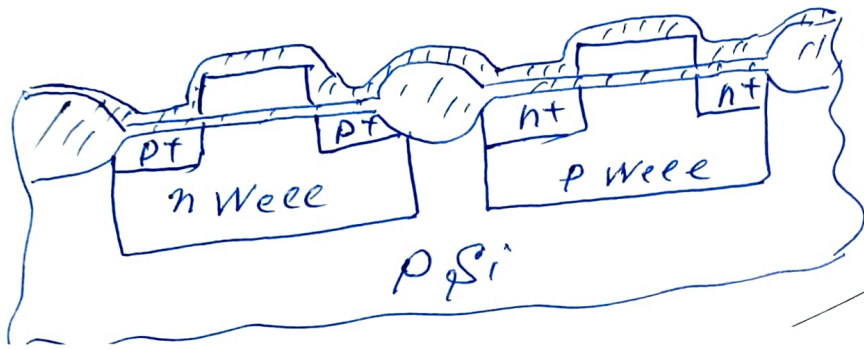
- 1) FL N4 pe poli Si
- 2) Inlaturarea FR



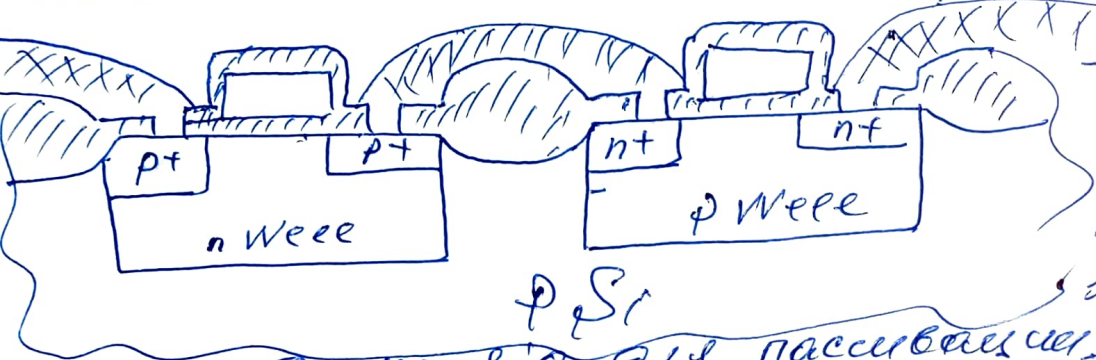
- 1) FL № 5
- 2) имплантация P₃₁⁺



- 1) FL № 6
- Имплантация Bi⁺



- 3) Окисление и осаднение SiO₂



- 1) FL № 7
- открытие контактных окон
- 2) нанесение Ae
- 3) FL № 8
- по Ae

- 4. Осаждение SiO₂ для passивации
- 5) FL № 9 открытие окон в контактах